

FDD6670A

N-Channel, Logic Level, PowerTrench® MOSFET

General Description

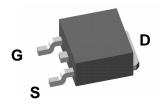
This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

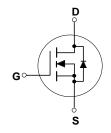
- DC/DC converter
- Motor drives

Features

- 66 A, 30 V. $R_{DS(on)}$ = 0.008 Ω @ V_{GS} = 10 V $R_{DS(on)}$ = 0.010 Ω @ V_{GS} = 4.5 V.
- Low gate charge (35nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R_{DS(on)}.



TO-252



Absolut	Tc=25°C unless otherwise not	ed	
Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	<u>±</u> 20	V
I _D	Maximum Drain Current -Continuous (Note 1)	66	А
	$T_A = 25^{\circ}C$ (Note 1a)	15	
	Maximum Drain Current -Pulsed	100	
P _D	Maximum Power Dissipation T _C = 25°C (Note 1)	70	W
	$T_A = 25^{\circ}C$ (Note 1a)	3.2	
	$T_A = 25^{\circ}C$ (Note 1b)	1.3	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

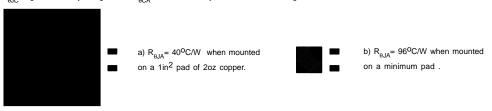
Thermal Characteristics									
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	°C/W					
$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	40	°C/W					
	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W					

Package Marking and Ordering Information								
Device Marking	Device	Reel Size	Tape width	Quantity				
FDD6670A	FDD6670A	13"	16mm	2500				

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain Ca	uras Avalanaka ratinga	(Alata 0)		I	l	<u>I</u>
W _{DSS}	Single Pulse Drain-Source	(Note 2) $V_{DD} = 15 \text{ V}, I_D = 66 \text{ A}$			400	mJ
I _{AR}	Avalanche Energy Maximum Drain-Source Avalance	L che Current			66	Α
	cteristics					I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
<u>A</u> BVdss ΔTJ	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		25		mV/º
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Chara	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.6	3	V
ΔVGS(th) ΛT,	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4		mV/°
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}$		0.0065 0.0090 0.0085	0.008 0.013 0.010	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	50			Α
g FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 12 \text{ A}$		55		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		3200		pF
Coss	Output Capacitance	f = 1.0 MHz		820		pF
C _{rss}	Reverse Transfer Capacitance	1		400		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		15	27	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		15	27	ns
t _{d(off)}	Turn-Off Delay Time	1		85	105	ns
t _f	Turn-Off Fall Time	1		42	68	ns
Q_g	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A},$		35	50	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$,		9		nC
Q_{gd}	Gate-Drain Charge			16		nC
Drain-So	urce Diode Characteristic	es and Maximum Ratings				
<u>Diaiii-30</u> I _s	Maximum Continuous Drain-So				2.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2.3 \text{ A} \text{ (Note 2)}$		0.72	1.2	V

Notes

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the drain tab. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

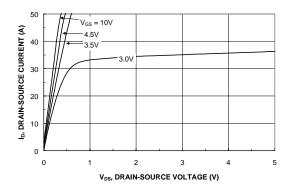


Figure 1. On-Region Characteristics.

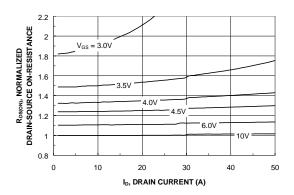


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

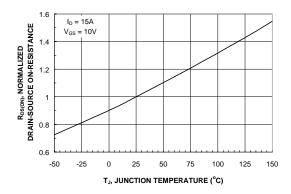


Figure 3. On-Resistance Variation with Temperature.

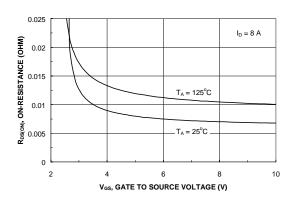


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

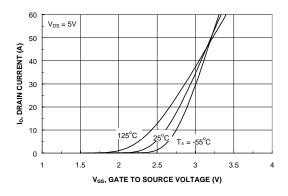


Figure 5. Transfer Characteristics.

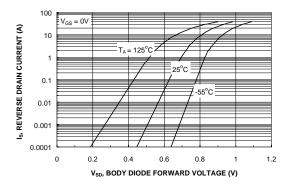
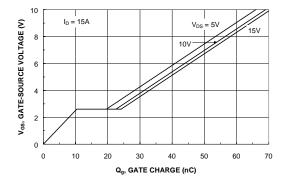


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



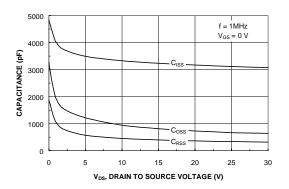
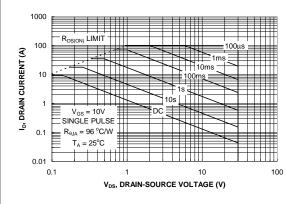


Figure 7. Gate-Charge Characteristics.

Figure 8. Capacitance Characteristics.



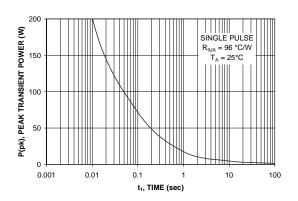


Figure 9. Maximum Safe Operating Area.



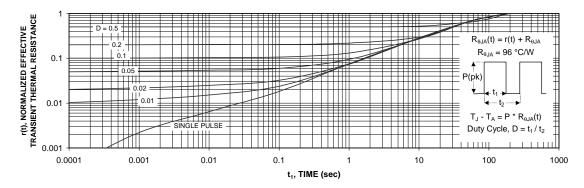
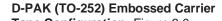


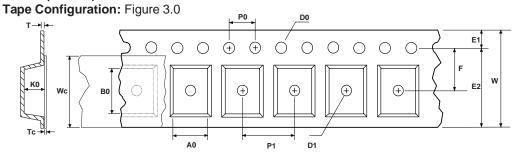
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient themal response will change depending on the circuit board design.

TO-252 Tape and Reel Data and Package Dimensions FAIRCHILD SEMICONDUCTOR TM D-PAK (TO-252) Packaging Configuration: Figure 1.0 Packaging Description: To-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13' or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table. Antistatic Cover Tape ESD Label These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped. Static Dissipative **Embossed Carrier Tape** F63TNR Label D-PAK (TO-252) Packaging Information Packaging Option D-PAK (TO-252) Unit Orientation Packaging type TNR Qty per Reel/Tube/Bag 2.500 Reel Size 13" Dia Box Dimension (mm) 359x359x57 5,000 Max qty per Box 359mm x 359mm x 57mm Weight per unit (gm) 0.300 Standard Intermediate box Weight per Reel(kg) 1.200 **ESD Label** F63TNR Label sample F63TNR Label D/C1: Z9942 D/C2: SPEC REV: CPN: QTY1: QTY2: TO-252 (D-PAK) Tape Leader and **Trailer Configuration:** Figure 2.0 \bigcirc \bigcirc \bigcirc \bigcirc \bigcirc 0 0 0 0 Components Trailer Tape 640mm minimum or 1680mm minimum or 80 empty pockets 210 empty pockets







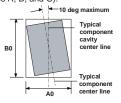
User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO252 (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



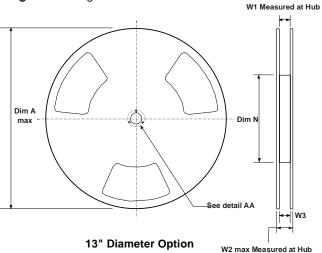
Sketch B (Top View)

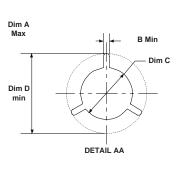
Component Rotation



Sketch C (Top View)
Component lateral movement

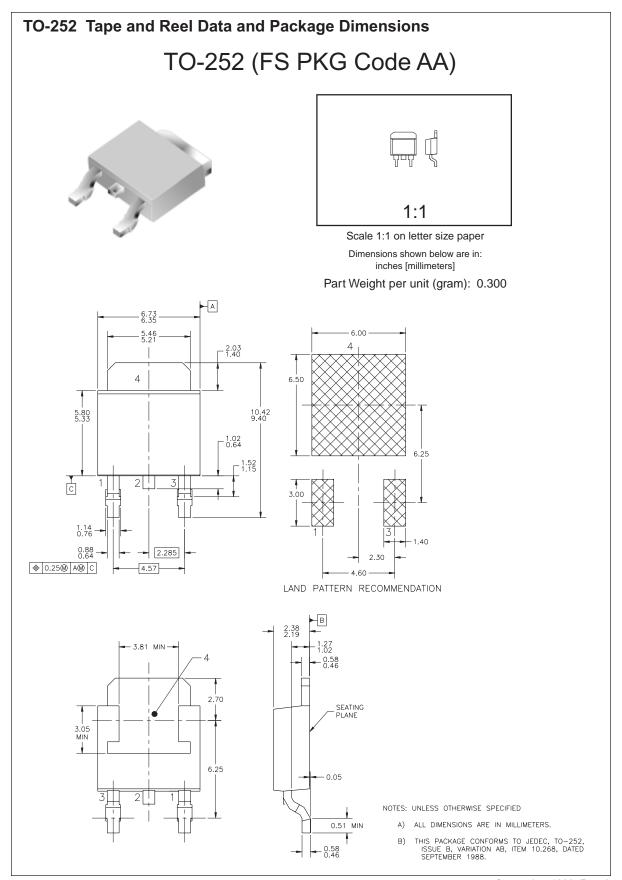
D-PAK (TO-252) Reel Configuration: Figure 4.0





3"	Diameter Option	W2 max Measured at Hu

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT $^{\text{TM}}$ QFET $^{\text{TM}}$ FACT Quiet Series $^{\text{TM}}$ QS $^{\text{TM}}$

 $\begin{array}{lll} \mathsf{FAST}^{\circledast} & \mathsf{Quiet}\,\mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}3} \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}6} \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}\text{-}8} \\ \end{array}$

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.